



UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/497,508	02/04/2000	Jin Jang	8733.20079	7572
30827	7590	11/01/2004	EXAMINER	
MCKENNA LONG & ALDRIDGE LLP			LOUIE, WAI SING	
1900 K STREET, NW			ART UNIT	
WASHINGTON, DC 20006			PAPER NUMBER	
			2814	

DATE MAILED: 11/01/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/497,508

Applicant(s)

JANG ET AL.

Examiner

Wai-Sing Louie

Art Unit

2814

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 23 August 2004.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 9-19 is/are pending in the application.
- 4a) Of the above claim(s) 14-19 is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 9-13 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some * c) ☐ None of:
1. ☒ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____ | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Miyanaga et al. (US 5,932,983) in view of Fonash et al. (US 5,994,164) and Kroontje et al. (US 4,940,923), newly cited.

With regard to claim 9, Miyanaga et al. disclose a semiconductor device having doped polycrystalline layer (col. 11, line 8 to col. 21, line 45) comprising:

- Containing metal atoms, nickel, having a density range of 1×10^{17} to 1×10^{20} atoms/cm³ on average, where the metal is a catalyst for metal induced crystallization of amorphous silicon (col. 8, lines 41-60, col. 11, lines 44-46 and fig. 4);
- The polycrystalline silicon film 104 is formed on an insulating substrate 101 (col. 11, lines 51-63);
- The polycrystalline silicon film comprises a plurality of the crystallites is needle-like (col. 7, lines 31-35);
- Miyanaga et al. do not disclose an electrical conductivity activation energy between 0.52 to 0.71 eV. However, Fonash et al. disclose forming a

- polycrystalline film with nickel as a catalyst element at low temperature annealing (Fonash col. 3, lines 38-49), where the conductivity activation energy is 0.52 eV @ 290°C (Fonash fig. 8b). Therefore, it would have been obvious in light of the teaching of Fonash et al. that the claimed activation energy is achieved when polycrystalline film has nickel as catalyst. Since the applicant has not established the criticality of the activation energy stated and since these values are in common use in similar devices in the art, it would have been obvious to one of ordinary skill in the art to use these values in the device. Where patentability is said to be based upon particular chosen dimension or upon another variable recited in a claim, the applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990);
- The thermal treatment with a lamp annealing process (col. 11 line 64 to col. 12, line 3), but do not disclose applying an electric field to the crystallization to the silicon. However, Kroontje et al. teach during operation of a lamp, a high-frequency electric field is generated (Kroontje col. 3, lines 6-7). Therefore, it would have been obvious for the one with ordinary skill in the art to recognize the electric field produced by the lamp is absorbed by silicon crystal during the formation of the polycrystalline silicon film 104.

With regard to claim 10, Miyanaga et al. disclose the metal is nickel (col. 11, lines 44-50).

With regard to claim 11, Miyanaga et al. disclose the metal works as a catalyst during crystallization (col. 11, line 11).

With regard to claim 12, Miyana et al. disclose a insulating (buffer) layer 102 between the substrate 101 and the crystalline (polycrystalline) silicon film 104 (fig. 1a).

With regard to claim 13, Miyana et al. disclose the needle-shaped silicon crystallites are formed by migration (movement) of a silicide of the metal (col. 7, lines 31-35 and col. 11, lines 44-46).

With regard to claim 14-19:

- Newly submitted claims 14-19 are directed to an invention that is independent or distinct from the invention originally claimed for the following reasons:

The original claims 1-9 are drawn to a semiconductor device and the newly added claims 10-13 are also drawn to a semiconductor device.

However, the newly added claims 14-19 are drawn to a method of forming the device, which is a distinct invention.

Since applicant has received an action on the merits for the originally presented invention, this invention has been constructively elected by original presentation for prosecution on the merits. Accordingly, claims 14-19 are withdrawn from consideration as being directed to a non-elected invention. *See 37 CFR 1.142(b) and MPEP § 821.03.*

Response to Arguments

Applicant's arguments filed 8/23/2004 have been fully considered but they are not persuasive.

- applicant argues that Miyanaga et al. do not teach or suggest an electric field applied to the amorphous silicon for crystallization. However, it is well known in the art that during operation of a lamp, a high-frequency electric field is generated such as disclose in Kroontje et al. (Kroontje col. 3, lines 6-7). Therefore, the high-frequency electric field is absorbed by silicon crystal during the formation of the polycrystalline silicon film.

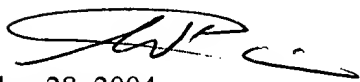
Any inquiry concerning this communication or earlier communications from the examiner should be directed to Wai-Sing Louie whose telephone number is (571) 272-1709. The examiner can normally be reached on 7:30 AM to 4:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Wsl

October 28, 2004.

A handwritten signature in black ink, appearing to be 'Wsl' or similar, written over the typed name 'Wsl'.